## IN THE CLAIMS:

Claim 1 (Currently Amended): An array substrate for a liquid crystal display device, comprising:

a gate line;

a data line including a first data line having a first width and a second data line having a second width overlying the first data line, the second width is larger than the first width;

a passivation layer between the first data line and the second data line;

a pixel electrode in a pixel region, the pixel region being defined by a crossing of the gate line and the data line, the pixel electrode being formed during a same process as the second data line; and

a thin film transistor connected to the pixel electrode.

Claim 2 (Currently Amended): The device according to claim 1, further includes appassivation layer between the first data line and the second data line, and at least one data contact hole in each pixel region for connecting the first data line to the second data line.

Claim 3 (Currently Amended): The device according to claim [[2]] 1, wherein the passivation layer interposed between the first data line and is disposed on the thin film transistor.

Claim 4 (Canceled).

Claim 5 (Original): The device according to claim 1, wherein the first data line includes

at least one of molybdenum (Mo), tungsten (W), chromium (Cr), and nickel (Ni).

Claim 6 (Original): The device according to claim 1, wherein the second data line and

the pixel electrode include at least a transparent conductive material.

Claim 7 (Original): The device according to claim 6, wherein the transparent conductive

material includes at least indium tin oxide (ITO).

Claim 8 (Original): The device according to claim 1, wherein the thin film transistor

includes the gate electrode, a first source electrode having a first width connected to the

first data line, a second source electrode having a second width connected to the second

data line, and a drain electrode spaced apart from the first source electrode.

Claim 9 (Original): The device according to claim 8, wherein the second source

electrode is formed over the first source electrode.

Claim 10 (Original): The device according to claim 9, wherein the second width of the

second source electrode is larger than the first width of the first source electrode.

Claim 11 (Withdrawn): A manufacturing method of an array substrate for a liquid crystal

display device, comprising:

forming a gate line on a transparent substrate, the gate line includes a gate

electrode;

forming a gate insulating layer and a semiconductor layer over the gate line;

forming a first data line having a first width and a drain electrode on the gate

insulating layer and on the semiconductor layer, the first data line includes a first source

electrode that crosses the gate line;

forming a passivation layer on the first source electrode, the first data line and the

drain electrode, the passivation layer includes a drain contact hole and a data contact

hole; and

forming a pixel electrode, a second data line having a second width and a second

source electrode, the pixel electrode connected to the drain electrode through the drain

contact hole, and the second data line connected to the first data line and the first source

electrode through the data contact hole.

Claim 12 (Withdrawn): The method according to claim 11, wherein the array substrate is

formed using a photolithographic masking process, and the pixel electrode, the second

data line and the second source electrode are simultaneously patterned during a same

light exposure process.

Claim 13 (Withdrawn): The method according to claim 11, wherein the second width of

the second data line is larger than the first width of the first data line.

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Claim 14 (Withdrawn): The method according to claim 9, wherein the pixel electrode, the second data line and the second source electrode include at least a transparent

conductive material.

Claim 15 (Withdrawn): The method according to claim 14, wherein the transparent

conductive material includes indium tin oxide (ITO).

Claim 16 (Withdrawn): The method according to claim 10, wherein the drain electrode,

the first data line and the first source electrode include at least one of molybdenum

(Mo), tungsten (W), chromium (Cr), and nickel (Ni).

Claim 17 (Withdrawn): A manufacturing method of an array substrate for a liquid crystal

display device, comprising:

forming a gate line;

forming a data line including a first data line having a first width and a second

data line having a second width larger than the first width;

forming a pixel electrode in a pixel region defined by a crossing of the gate line

and the data line; and

forming a thin film transistor connected to the pixel electrode.

Claim 18 (Withdrawn): The method according to claim 17, wherein the pixel electrode

and the second data line are simultaneously formed during a same process.

Claim 19 (Withdrawn): The method according to claim 17, further includes forming an

insulating layer between the first data line and the second data line

Claim 20 (Withdrawn): The method according to claim 19, further includes forming at

least one data contact hole in each pixel region for connecting the first data line and

the second data line.

Claim 21 (Withdrawn): The method according to claim 19, further includes forming a

passivation layer between the first data and the second data line on the thin film

transistor.

Claim 22 (Withdrawn): The method according to claim 21, wherein the passivation layer

and the insulating layer are simultaneously formed during a same process.

Claim 23 (Withdrawn): The method according to claim 17, wherein the first data line

includes at least one of molybdenum (Mo), tungsten (W), chromium (Cr), and nickel

(Ni).

Claim 24 (Withdrawn): The method according to claim 17, wherein the second data line

and the pixel electrode include at least a transparent conductive material.

Claim 25 (Withdrawn): The method according to claim 24, wherein the transparent

conductive material includes at least indium tin oxide (ITO).

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Claim 26 (Withdrawn): The method according to claim 17, wherein forming the thin

film transistor includes forming a first source electrode having a first width connected to

the first data line, forming a second source electrode having a second width connected to

the second data line, and forming a drain electrode spaced apart from the first source

electrode.

Claim 27 (Withdrawn): The method according to claim 26, wherein the second source

electrode is formed over the first source electrode.

Claim 28 (Withdrawn): The method according to claim 27, wherein the second width of

the second source electrode is larger than the first width of the first source electrode.